

**60V Dual N-Channel Enhancement Mode MOSFET****Description**

The PECN4826SR uses advanced trench technology to provide excellent  $R_{DS(ON)}$  with low gate charge.

This device is suitable for high side switch in SMPS and general purpose applications.

**General Features**

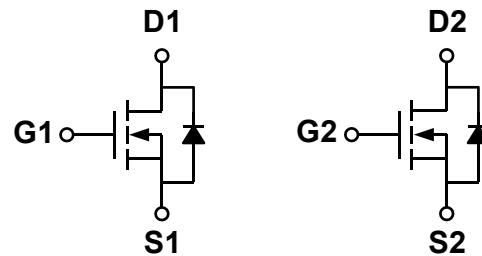
- ◆  $V_{DS} = 60V, ID = 6A$   
 $R_{DS(ON)} = 19m\Omega$  (typical) @  $VGS = 10V$   
 $R_{DS(ON)} = 22m\Omega$  (typical) @  $VGS = 4.5V$
- ◆ Excellent gate charge  $\times R_{DS(ON)}$  product(FOM)
- ◆ Very low on-resistance  $R_{DS(ON)}$
- ◆ 150 °C operating temperature
- ◆ Pb-free lead plating

**Application**

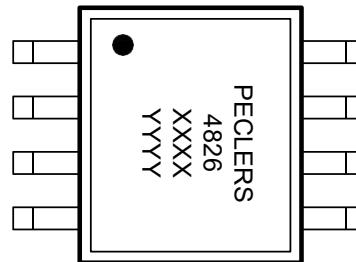
- ◆ DC/DC Converter
- ◆ Ideal for high-frequency switching and synchronous rectification

**Package**

- 100% UIS TESTED!
- 100%  $\Delta Vds$  TESTED!

**Schematic diagram****Marking and pin assignment**

SOP-8  
(TOP VIEW)



Note:

XXXX is the Wafer Information

YYYY is the Quality Code

**Ordering Information**

Part Number	Storage Temperature	Package	Devices Per Reel
PECN4826SR	-55°C to +150°C	SOP-8	4000

**Absolute Maximum Ratings (TA=25°C unless otherwise noted)**

parameter	symbol	limit	unit
Drain-source voltage	$V_{DS}$	60	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous (Silicon Limited)	$I_D$	6	A
		4	
Pulsed Drain Current (Package Limited)	$I_{DM}$	24	A
Single pulse avalanche energy( $L=0.5mH$ )	$E_{AS}$	80	mJ
Maximum power dissipation	$P_D$	2	W
		1.3	
Operating junction Temperature range	$T_j$	-55—150	°C

**Electrical Characteristics** (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF Characteristics</b>						
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	-	-	V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
<b>ON Characteristics</b>						
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2	1.9	2.5	V
Drain-source on-state resistance	R <sub>D(S)ON</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A	-	19	25	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	22	28	
Forward transconductance	g <sub>fS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =6A	-	28	-	S
<b>Dynamic Characteristics</b>						
Input capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V f=1.0MHz	-	1900	2250	pF
Output capacitance	C <sub>OSS</sub>		-	150	-	
Reverse transfer capacitance	C <sub>RSS</sub>		-	115	-	
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1.0MHz	-	5	8	Ω
<b>Switching Characteristics</b>						
Turn-on delay time	t <sub>D(ON)</sub>	V <sub>DS</sub> =30V V <sub>GS</sub> =10V R <sub>L</sub> =1.5Ω R <sub>GEN</sub> =3Ω	-	7.5	-	ns
Rise time	tr		-	5	-	
Turn-off delay time	t <sub>D(OFF)</sub>		-	28	-	
Fall time	tf		-	5.5	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =6A V <sub>GS</sub> =10V	-	46	-	nC
Gate-source charge	Q <sub>gs</sub>		-	6	-	
Gate-drain charge	Q <sub>gd</sub>		-	14.2	-	

**Thermal Characteristics**

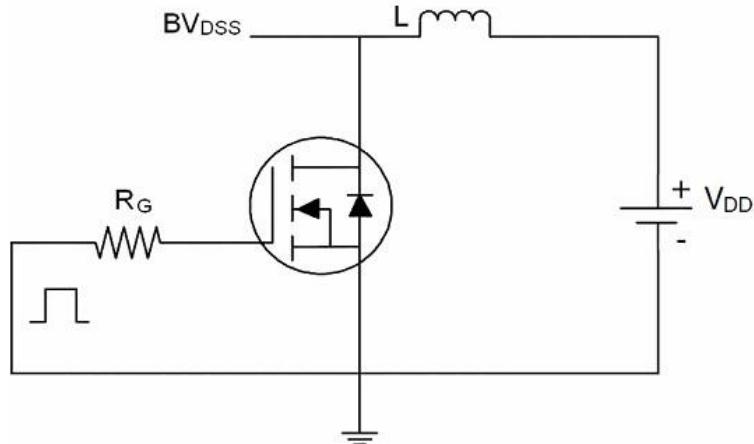
Parameter	Symbol	Typ	Max	Unit
Maximum Junction-to-Ambient <sup>A</sup>	≤ 10s	R <sub>θJA</sub>	33	40
Maximum Junction-to-Ambient <sup>A</sup>	Steady-State		59	75
Maximum Junction-to-Lead <sup>B</sup>	Steady-State		16	24

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

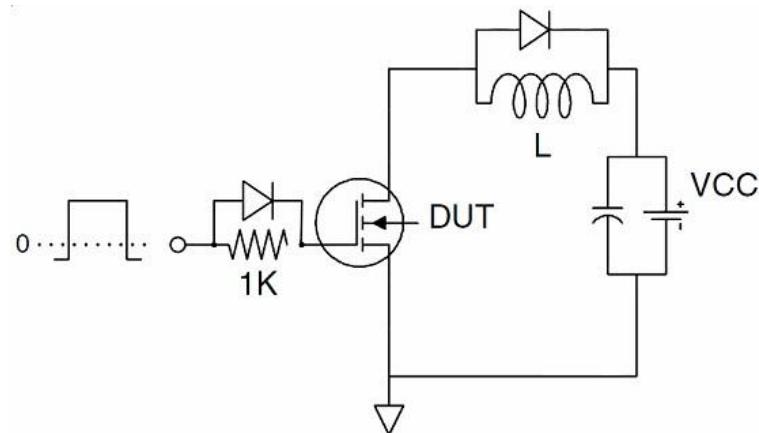
B: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJC</sub> and lead to ambient.

### Test Circuit:

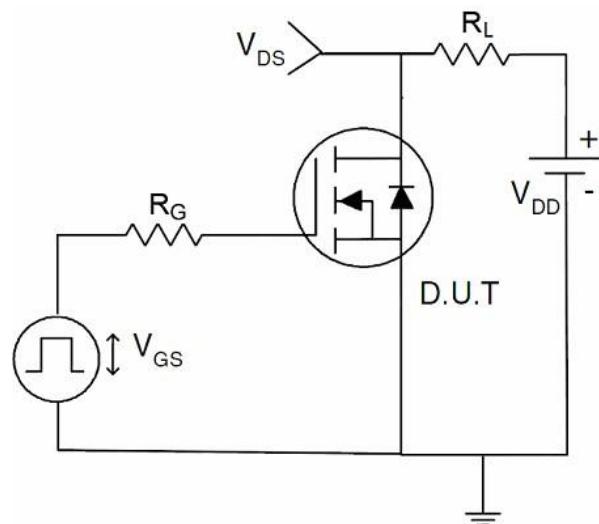
(1) 、 EAS Test Circuit



(2) 、 Gate Charge Test Circuit

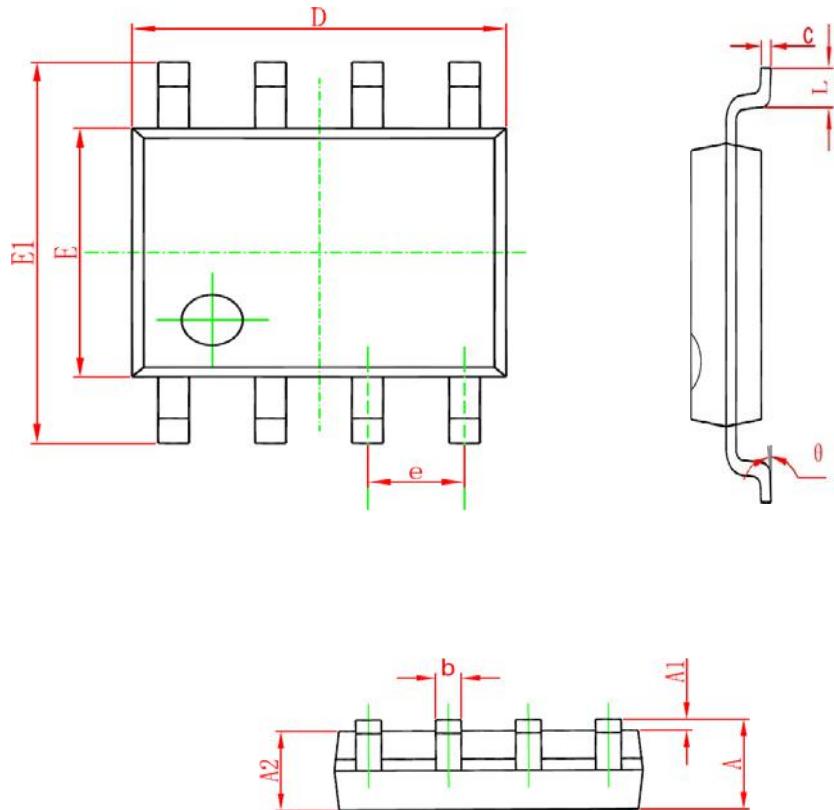


(3) 、 Switch Time Test Circuit



## Package Information

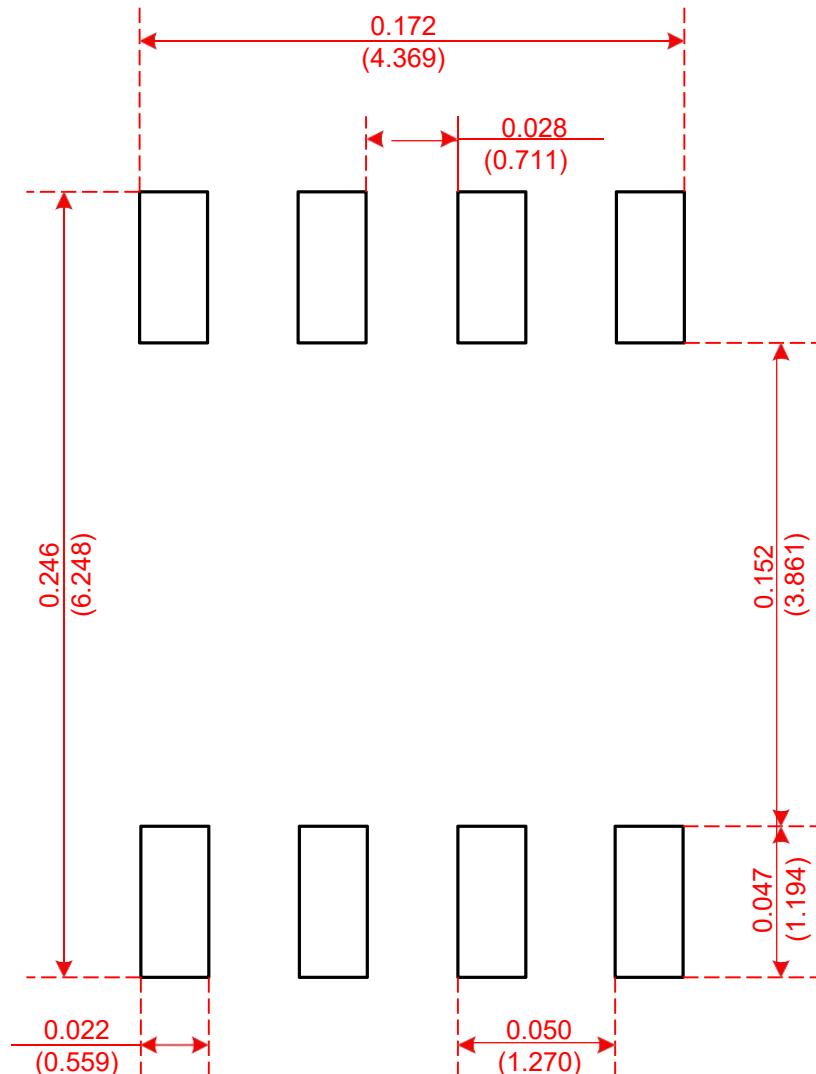
- SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

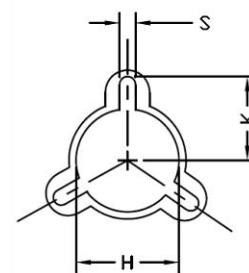
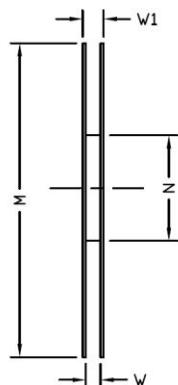
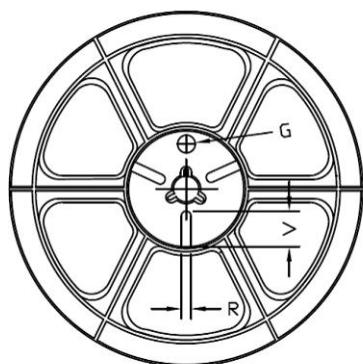
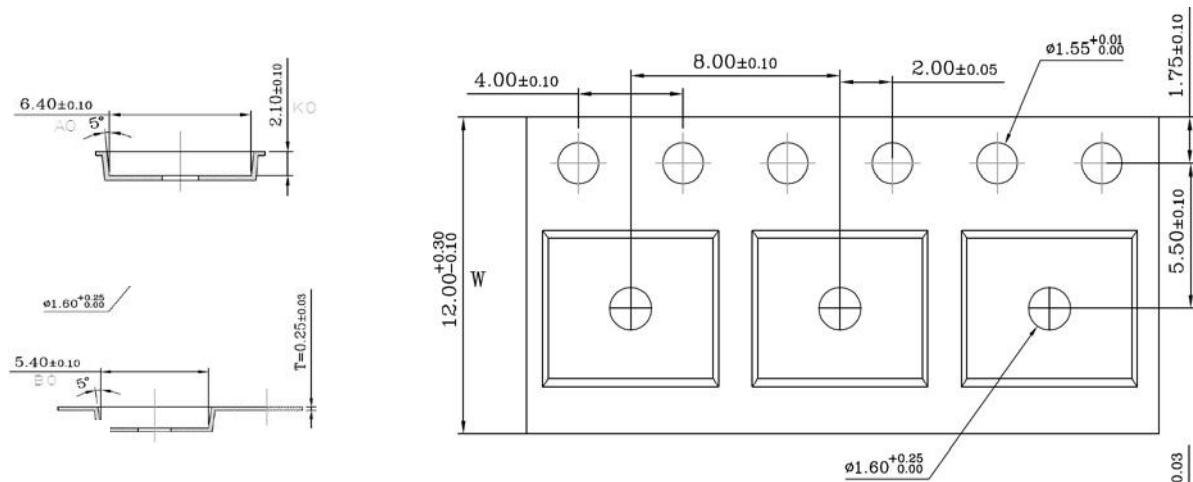
### Recommended Minimum Pads

- SOP-8



### Tape and Reel

- SOP-8



Tape Size	Reel Size	M	N	W	W1	H	K	S	G	R	V
12mm	Ø330	Ø330.00 ±0.50	Ø97.00 ±0.30	13.00 ±0.30	17.40 ±1.00	Ø13.00 ±0.5	10.6	2.00 ±0.50	—	—	—

